Electronic Supplementary Information

Metal-Insulator Transition in Multilayer MoS$_2$

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Figure S1 Temperature dependence of $I$-$V$ curves measured for (a) device II, (b) device III, and (c) device IV. $\ln(I/T^2)$ versus $1000/T$ for (d) device II, (e) device III, and (f) device IV. Slope estimated from the plot of $\ln(I/T^2)$ versus $1000/T$ as a function of $V$ for (g) device II and (h) device III.
Figure S2 (a) \( I-V \) curves measured at different temperatures for device V. (b) \( I-V_G \) transfer curves of device V at different temperatures with \( V = 0.5 \) V and (c) \( V = -0.5 \) V. \( \ln(I/T^2) \) vs 1000/\( T \) for (d) positive and (e) negative voltages. (f) Slope estimated from \( \ln(I/T^2) \) versus 1000/\( T \) as a function of \( V \) for negative voltages.
Figure S3. $I$-$V_G$ transfer curves measured for devices VI (2.3 nm), VII (12 nm), and VIII (16 nm) with different thicknesses before (a, c, e) and after (b, d, f) RTA.